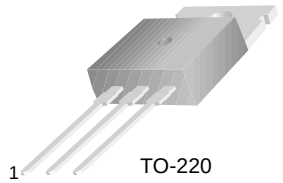
FAIRCHILD
SEMICONDUCTOR TM

KSB546

TV Vertical Deflection Output

- Collector-Base Voltage : V_{CBO} = -200V
- Collector Current : I_C = -2A
- Collector Dissipation : P_C= 25W (T_C=25°C)
- Complement to KSD401



TO-220

1.Base 2.Collector 3.Emitter

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	- 200	V
V_{CEO}	Collector-Emitter Voltage	- 150	V
V_{EBO}	Emitter-Base Voltage	- 5	V
I_C	Collector Current(DC)Y	- 2	A
P_C	Collector Dissipation (T_C=25°C)	25	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	I_C = - 500μA, I_E = 0	- 200			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = - 10mA, I_B = 0	- 150			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = - 500uA, I_C = 0	- 5			V
I_{CBO}	Collector Cut-off Current	V_{CB} = - 150V, I_E = 0			- 50	μA
h_{FE}	DC Current Gain	V_{CE} = - 10V, I_E = - 0.4A	40		240	
V_{CE}(sat)	Collector-Emitter Saturation Voltage	I_C = - 500mA, I_B = - 50mA			- 1	V
f_T	Current Gain Bandwidth Product	V_{CE} = - 10V, I_C = - 0.4A		5		MHz

h_{FE} Classification

Classification	R	O	Y
h_{FE}	40 ~ 80	70 ~ 140	120 ~ 240

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Typical Characteristics

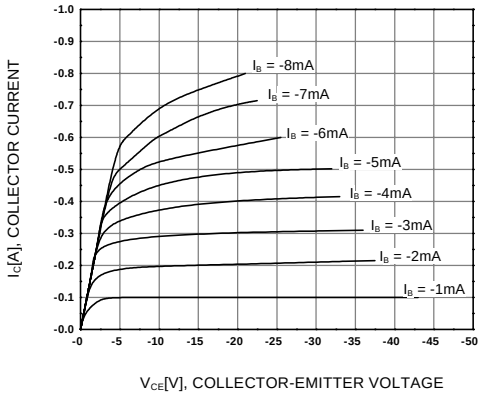


Figure 1. Static Characteristic

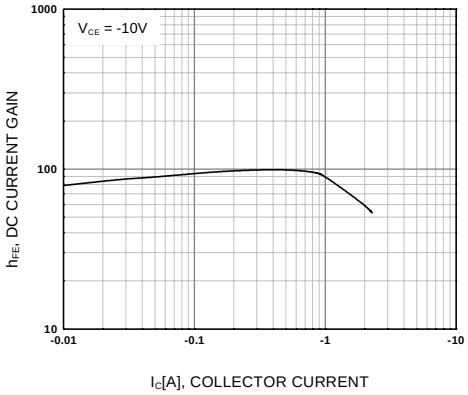


Figure 2. DC current Gain

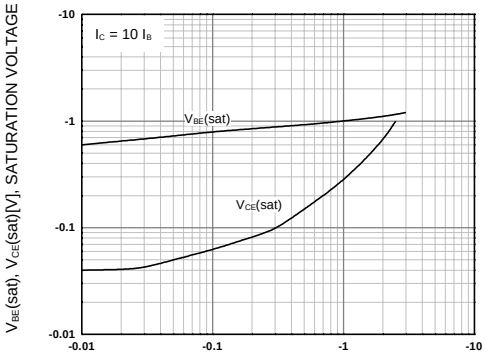


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

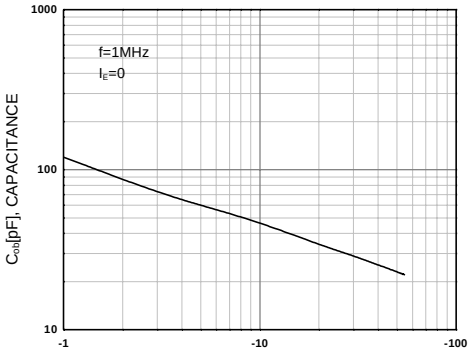


Figure 4. Collector Output Capacitance

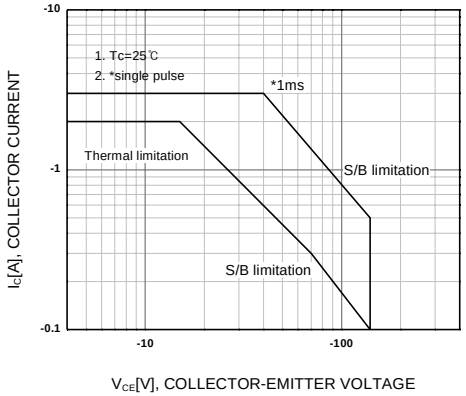


Figure 5. Safe Operating Area

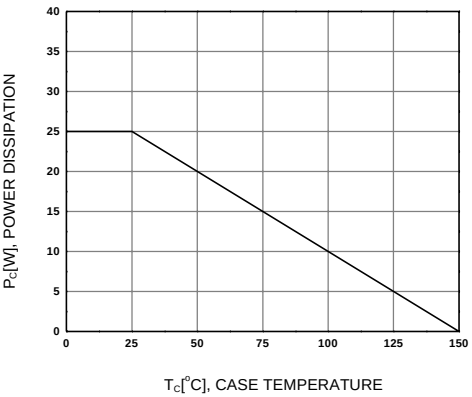
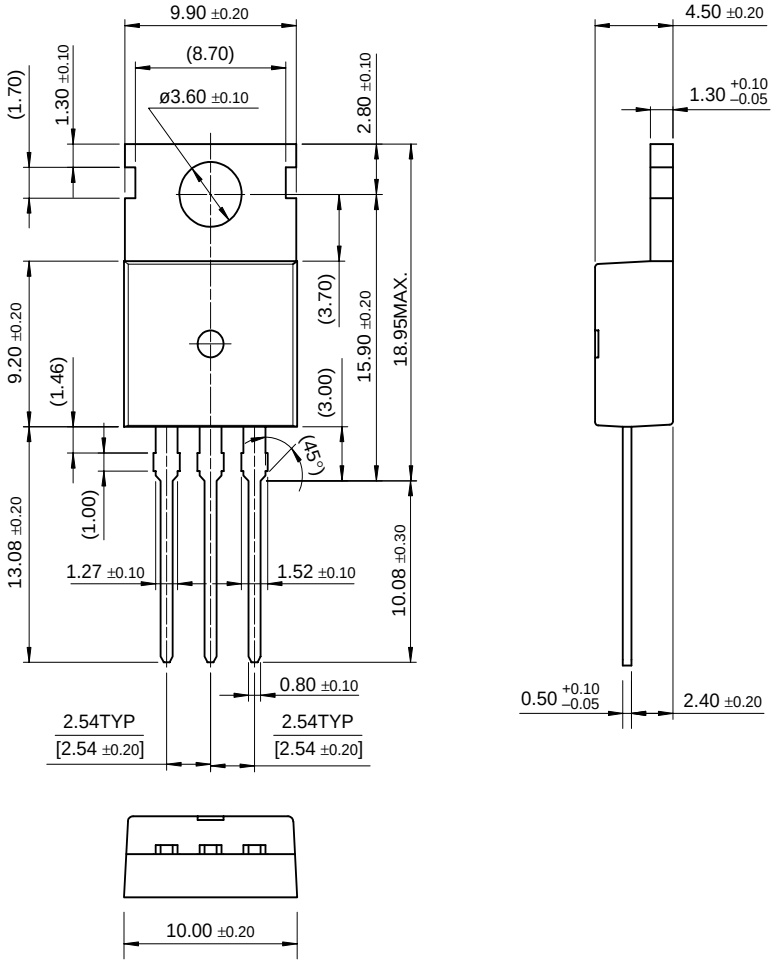


Figure 6. Power Derating

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Package Demensions

TO-220



Dimensions in Millimeters

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

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KSB546

PNP Epitaxial Silicon Transistor

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Features

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- Collector Current: I_C=-2A
- Collector Dissipation: P_C=25W (T_C=25°C)
- Complement to KSD401

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Applications

TV Vertical Deflection Output

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Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSB546YTU	Full Production	$0.364	TO-220	3	RAIL
KSB546O	Full Production	$0.364	TO-220	3	BULK
KSB546R	Full Production	$0.364	TO-220	3	BULK
KSB546Y	Full Production	$0.364	TO-220	3	BULK

* 1,000 piece Budgetary Pricing

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